

A cross-sectional view of a semiconductor device. The top surface is labeled 40. Below it are three horizontal regions labeled 42, 46, and 44 from left to right. A layer labeled S2 is shown below these regions. Below S2 are two more layers labeled I2 and H.B., both containing underlined labels 72 and 70 respectively. These layers are curved over a central region. Below them is a stack of four horizontal layers labeled 56, 50, 54, and 48 from top to bottom. To the left of this stack is a label I1, and to the right is a bracketed group containing 56, 50, and 54. Further to the right is a label 74. The central part of the stack is connected by a vertical line labeled 68. On the right side of the stack, there are four horizontal lines labeled 66, 58, 60, and 62 from top to bottom. To the right of these lines is a label 52. At the bottom of the diagram is a large rectangular region labeled S1. Above S1, centered under the stack, is a label 64.

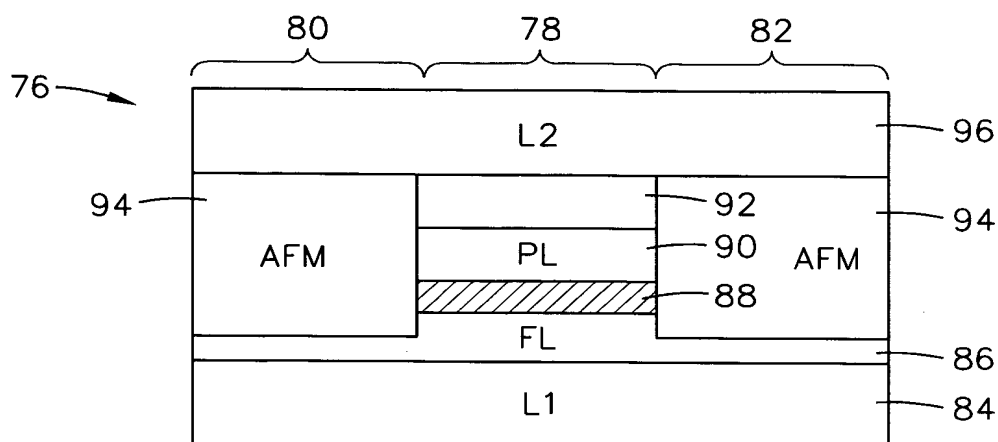


FIG. 2A

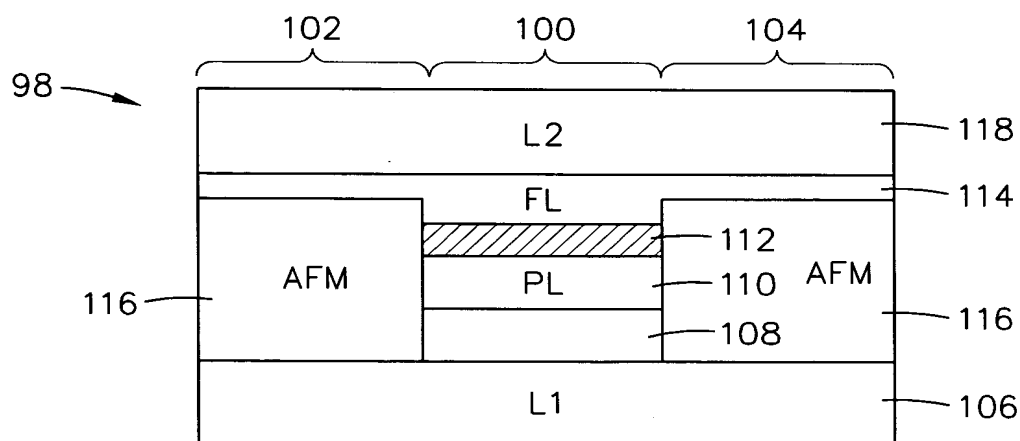


FIG. 2B

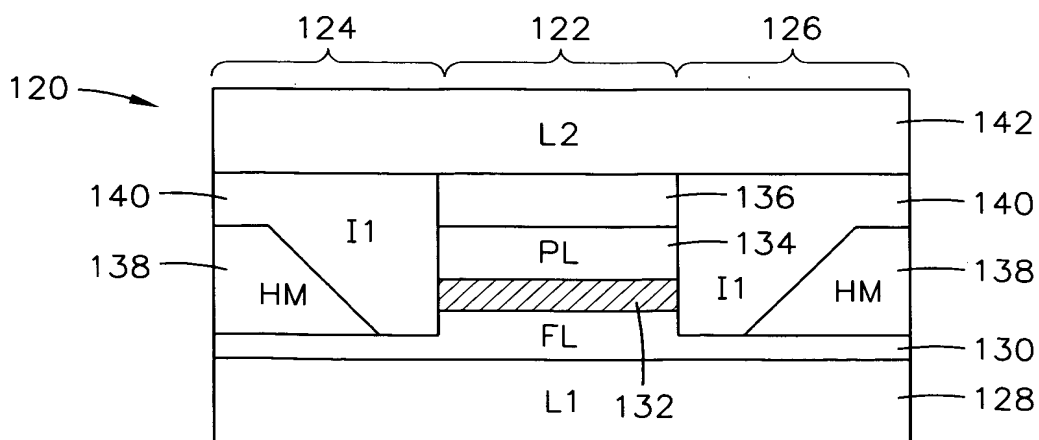


FIG. 3A

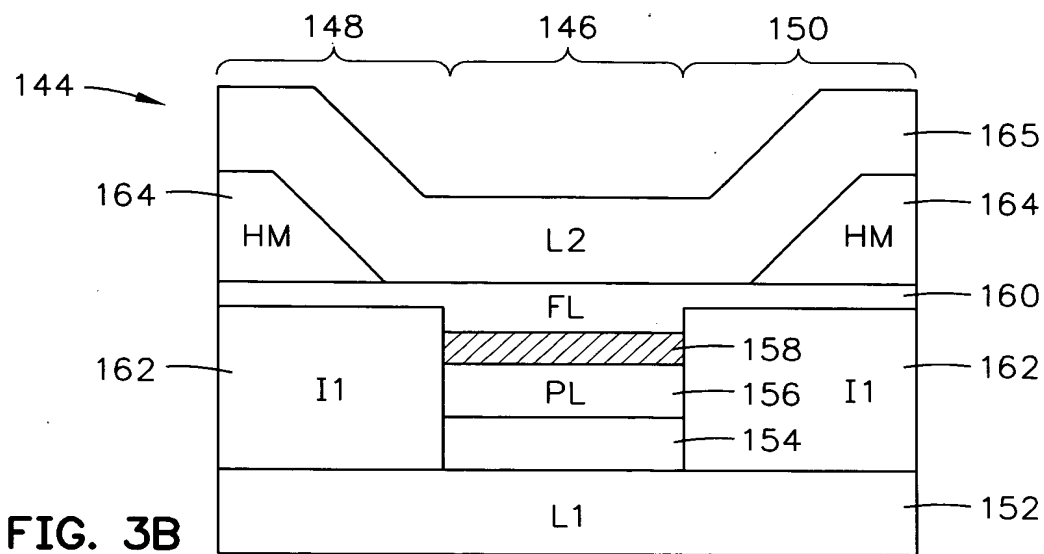


FIG. 3B

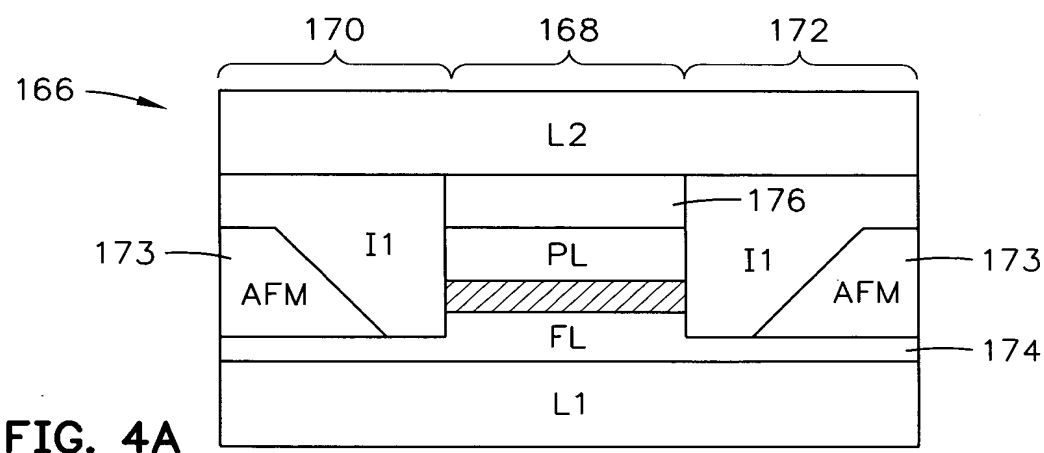


FIG. 4A

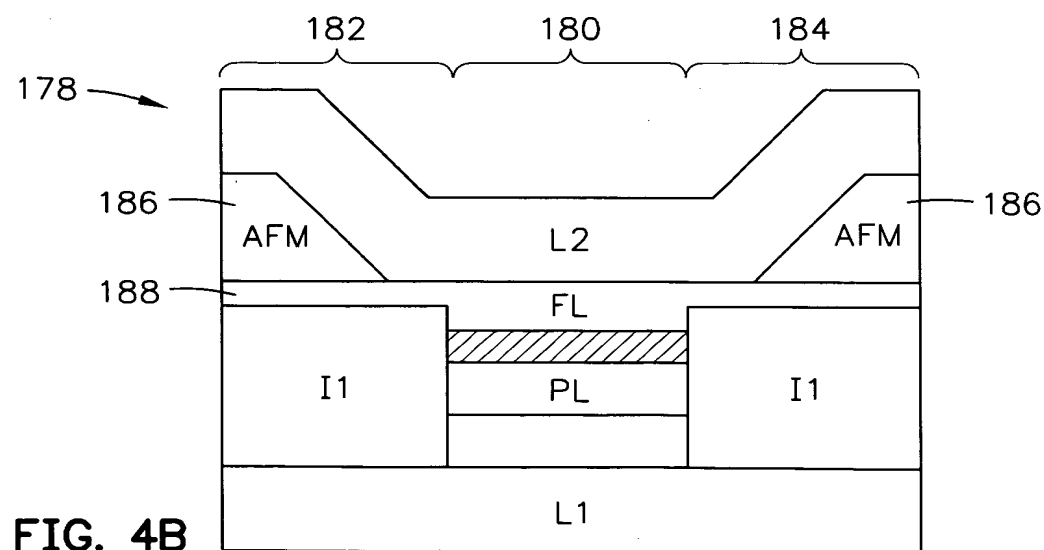


FIG. 4B

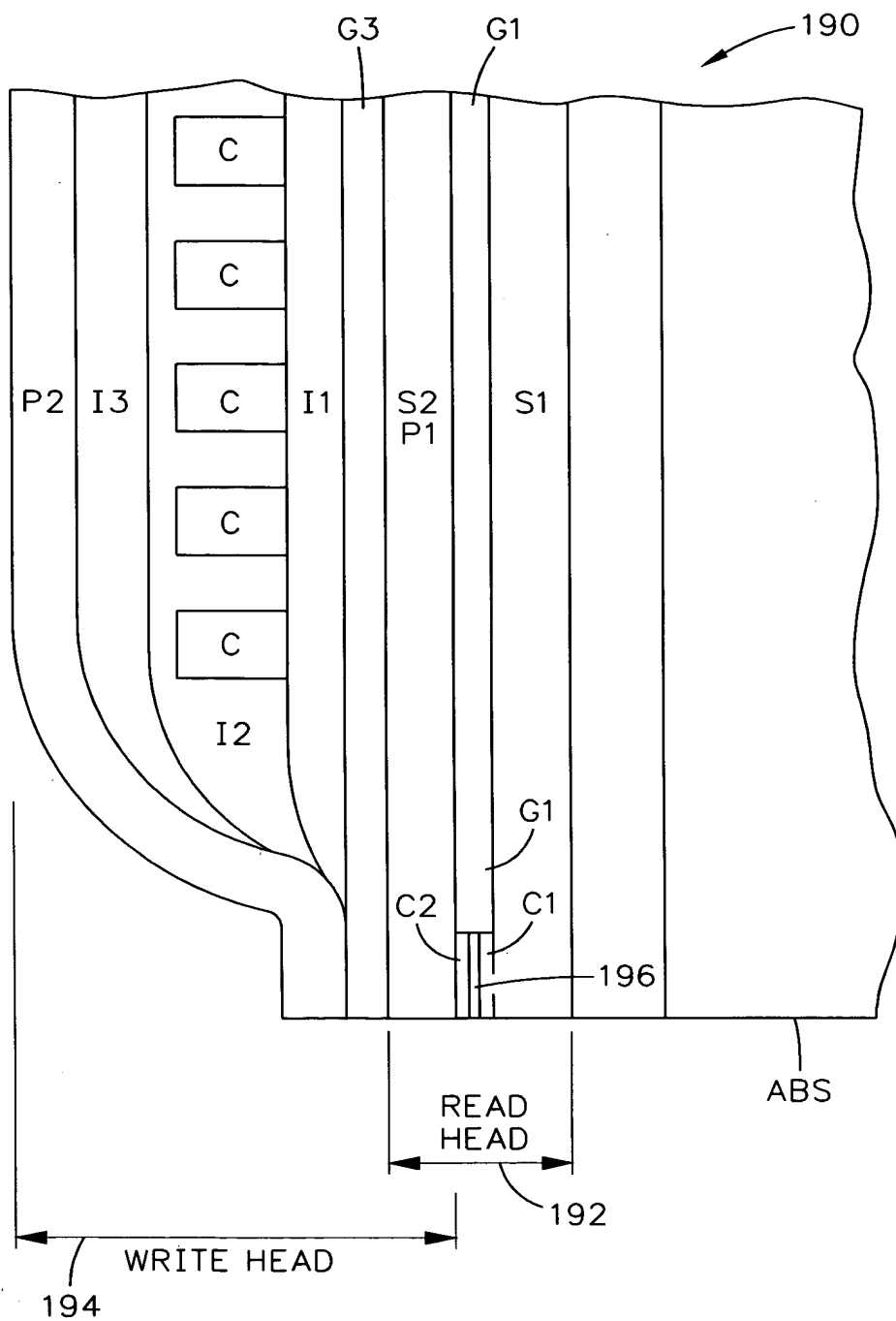


FIG. 5

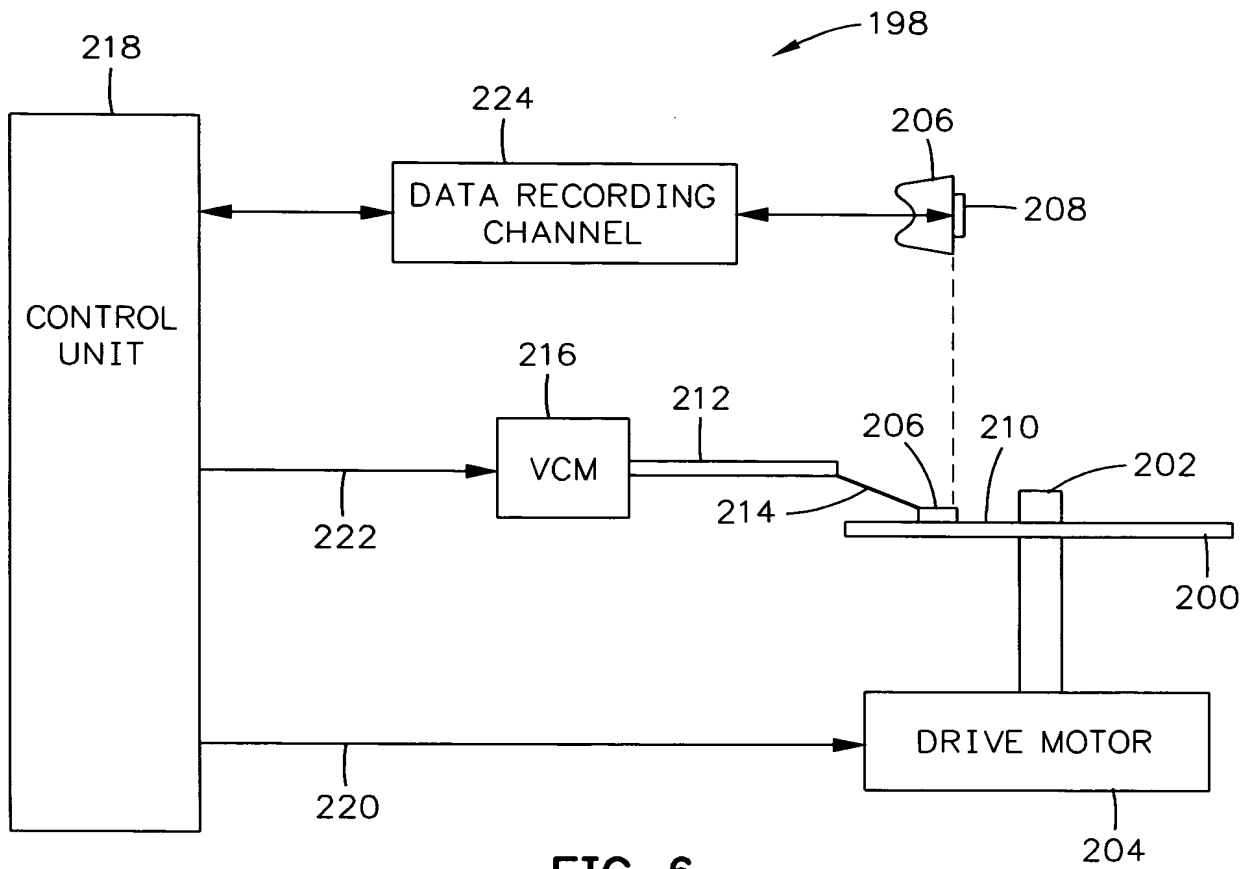


FIG. 6

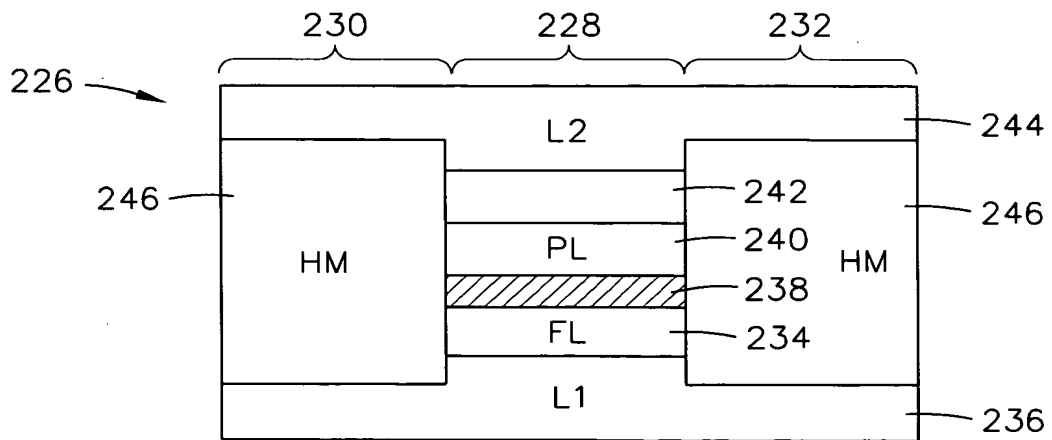


FIG. 7

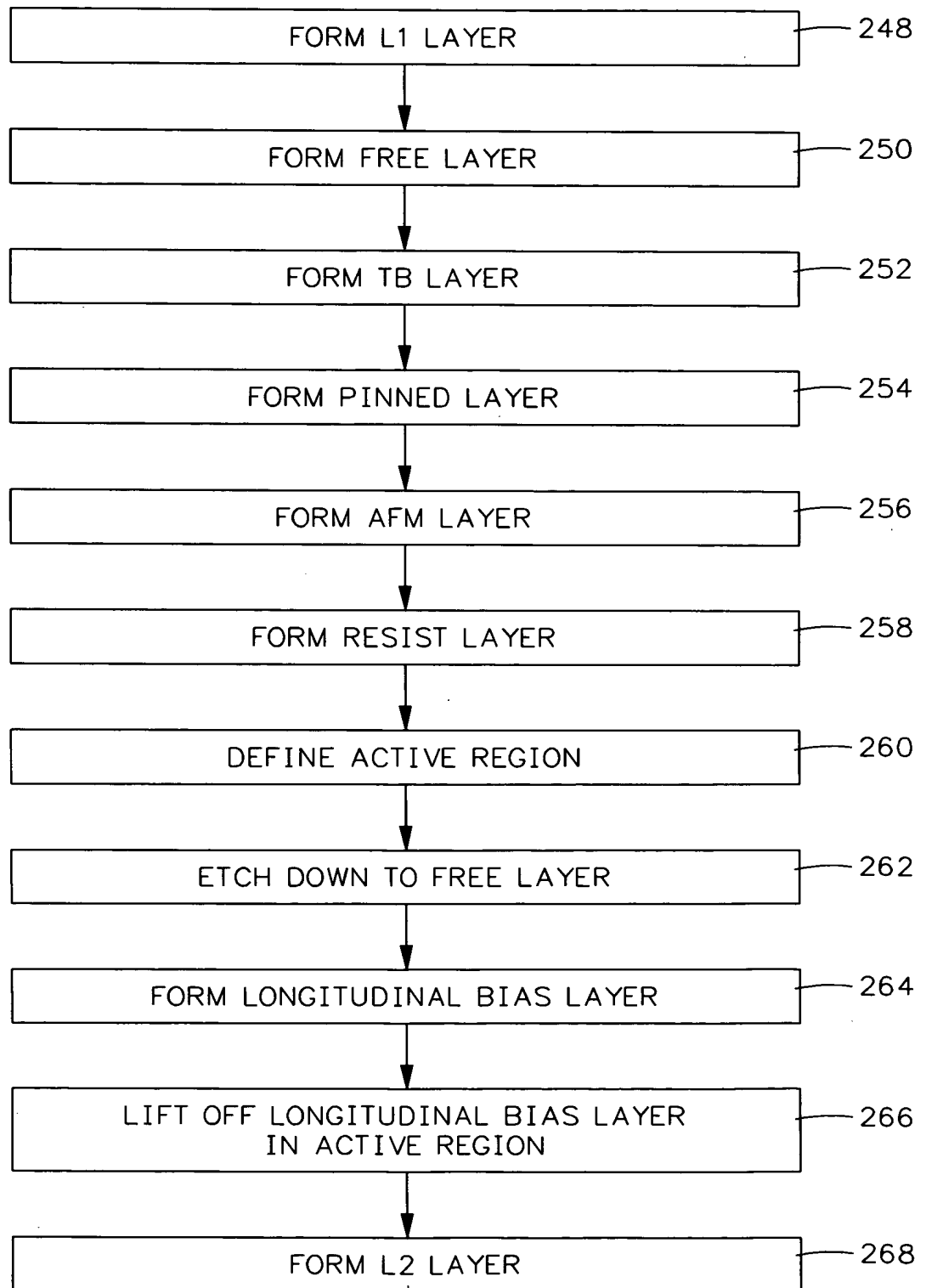


FIG. 8